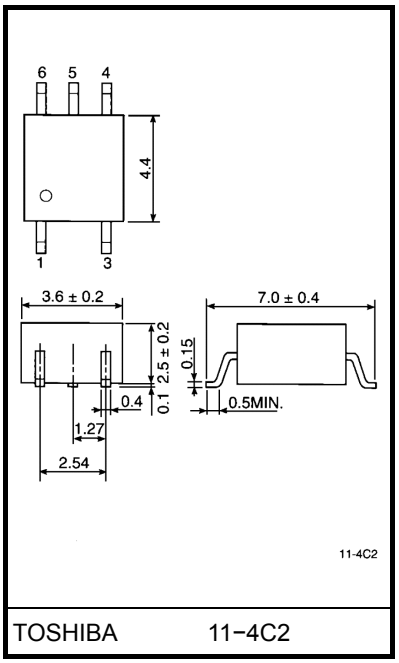
TOSHIBA Photocoupler GaAs Ired & Photo−Transistor

TLP131

Unit in mm



TOSHIBA 11−4C2

Weight: 0.09 g

Office Machine

Programmable Controllers

AC / DC−Input Module

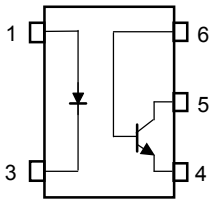
Telecommunication

The TOSHIBA mini flat coupler TLP131 is a small outline coupler, suitable for surface mount assembly.
TLP131 consists of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

- Collector−emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)
  Rank GB: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349

TLP131 base terminal is for the improvement of speed, reduction of dark current, and enable operation.

Pin Configurations (top view)



1 : Anode
3 : Cathode
4 : Emitter
5 : Collector
6 : Base

Current Transfer Ratio

Type	Classification	Current Transfer Ratio (%) (I_C / I_F) I_F = 5mA, V_{CE} = 5V, Ta = 25°C		Marking Of Classification
		Min.	Max.	
TLP131	(None)	50	600	BLANK, Y, Y■, G, G■, B, B■, GB
	Rank Y	50	150	Y, Y■
	Rank GR	100	300	G, G■
	Rank GB	100	600	G, G■, B, B■, GB

Note: Application type name for certiffication test,please use standard product type name,i.e.
TLP131(GB): TLP131

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta≥53°C)	ΔI_F / °C	−0.7	mA / °C
	Peak forward current (100μs pulse,100pps)	I_{FP}	1	A
	Reverse voltage	V_R	5	V
	Junction temperature	T_j	125	°C
Detector	Collector−emitter voltage	V_{CEO}	80	V
	Collector−base voltage	V_{CBO}	80	V
	Emitter−collector voltage	V_{ECO}	7	V
	Emitter−base voltage	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Peak collector current (10ms pulse,100pps)	I_{CP}	100	mA
	Power dissipation	P_C	150	mW
	Power dissipation derationg (Ta ≥ 25°C)	ΔP_C / °C	−1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	−55~125	°C
Operating temperature range		T_{opr}	−55~100	°C
Lead soldering temperature (10s)		T_{sol}	260	°C
Total package power dissipation		P_T	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP_T / °C	−2.0	mW / °C
Isolation voltage (AC, 1min., RH≤ 60%) (Note 1)		BV_S	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins 1 and 3 shorted together, and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	48	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	−25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	—	pF
Detector	Collector−emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 0.5mA	80	—	—	V
	Emitter−collector breakdown voltage	$V_{(BR)ECO}$	I_E = 0.1mA	7	—	—	V
	Collector−base breakdown voltage	$V_{(BR)CBO}$	I_C = 0.1mA	80	—	—	V
	Emitter−base breakdown voltage	$V_{(BR)EBO}$	I_E = 0.1mA	7	—	—	V
	collector dark current	I_{CEO}	V_{CE} = 48V	—	10	100	nA
			V_{CE} = 48V,Ta = 85°C	—	2	50	μA
	Collector dark current	I_{CER}	V_{CE} = 48V,Ta = 85°C R_{BE} = 1MΩ	—	0.5	10	μA
	Collector dark current	I_{CBO}	V_{CB} = 10V	—	0.1	—	nA
	DC forward current gain	h_{FE}	V_{CE} = 5V,I_C = 0.5mA	—	400	—	—
	Capacitance (collector to emitter)	C_{CE}	V = 0, f = 1MHz	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	I_F = 5 mA, V_{CE} = 5 V	50	—	600	%
		Rank GB	100	—	600	
Saturated CTR	I_C / $I_{F\ (sat)}$	I_F = 1 mA, V_{CE} = 0.4 V	—	60	—	%
		Rank GB	30	—	—	
Base photo−current	I_{PB}	I_F = 5mA,V_{CB} = 5V	—	10	—	μA
Collector−emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 2.4 mA, I_F = 8 mA	—	—	0.4	V
		I_C = 0.2 mA, I_F = 1 mA	—	0.2	—	
		Rank GB	—	—	0.4	
Off−state collector current	$I_{C\ (off)}$	I_F = 0.7mA, V_{CE} = 48 V	—	1	10	μA

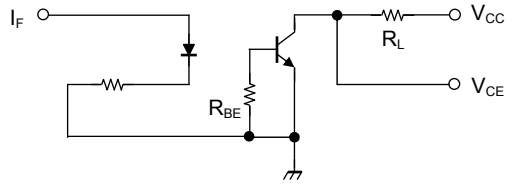
Isolation Characteristics (Ta = 25°C)

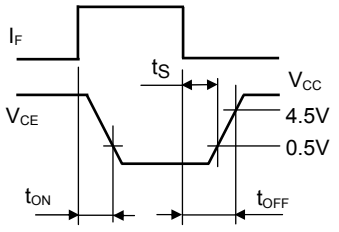
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C_S	V_S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	3750	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

Switching Characteristics (Ta = 25°C)

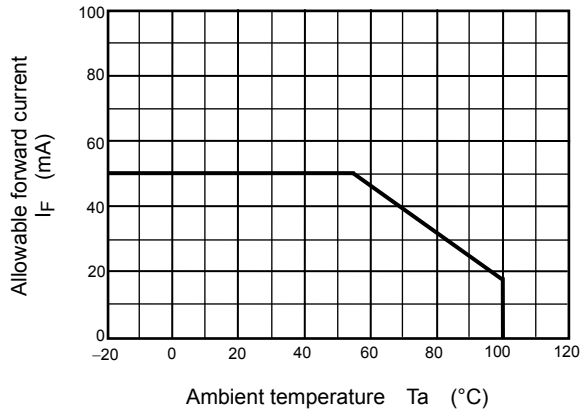
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100Ω	—	2	—	μs
Fall time	t_f		—	3	—	
Turn−on time	t_{on}		—	3	—	
Turn−off time	t_{off}		—	3	—	
Turn−on time	t_{ON}	R_L = 1.9 kΩ%) (Fig.1) R_{BE} = OPEN V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	25	—	
Turn−off time	t_{OFF}		—	40	—	
Turn−on time	t_{ON}	R_L = 1.9 kΩ%) (Fig.1) R_{BE} = 220 kΩ V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	20	—	
Turn−off time	t_{OFF}		—	30	—	

Fig. 1 Switching time test circuit

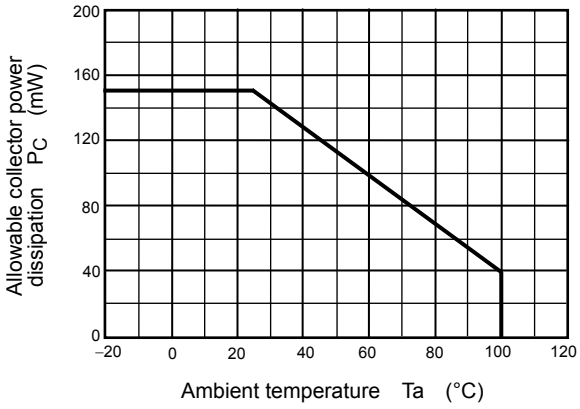




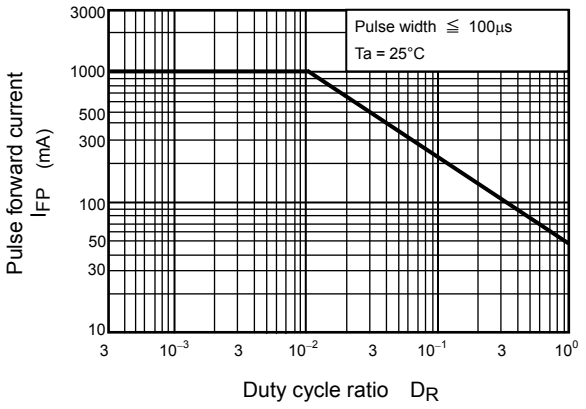
I_F – Ta



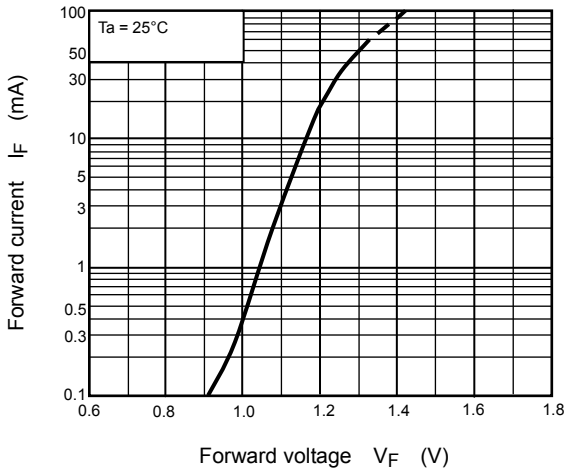
P_C – Ta



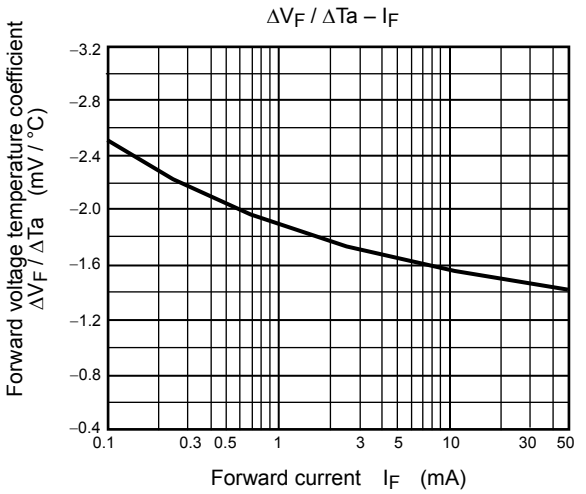
I_{FP} – D_R



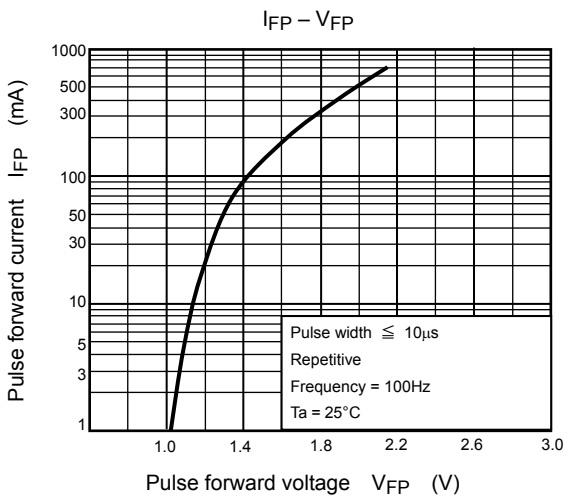
I_F – V_F



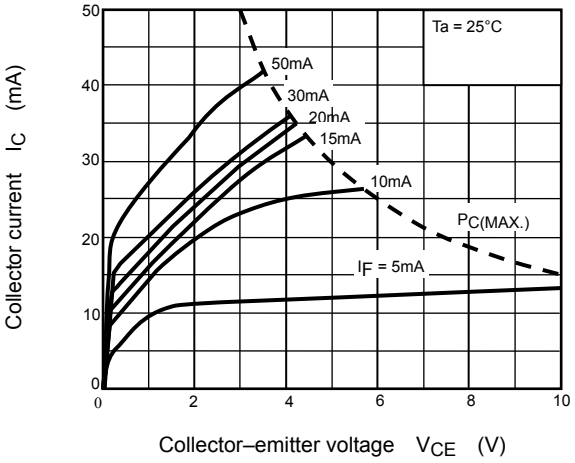
$\Delta V_F / \Delta Ta$ – I_F



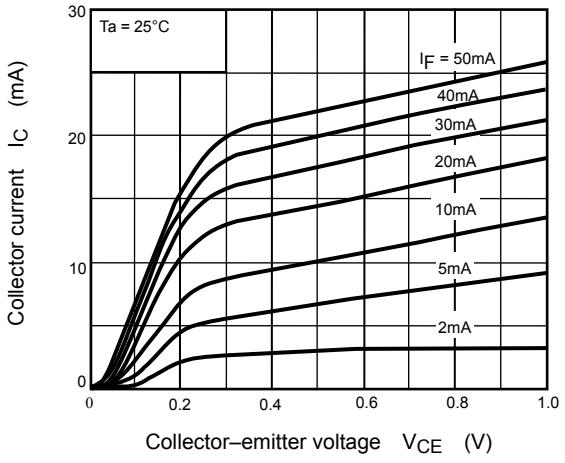
I_{FP} – V_{FP}



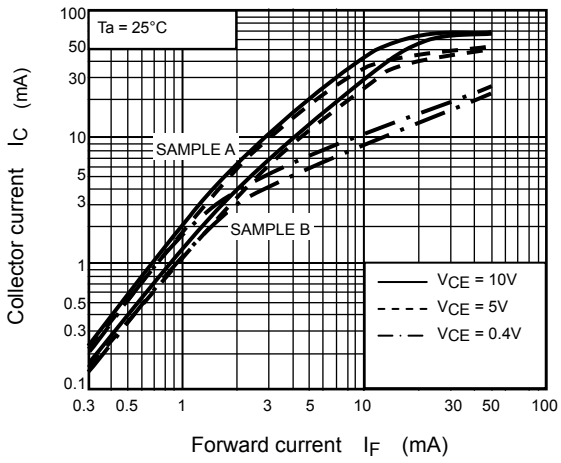
$I_C - V_{CE}$



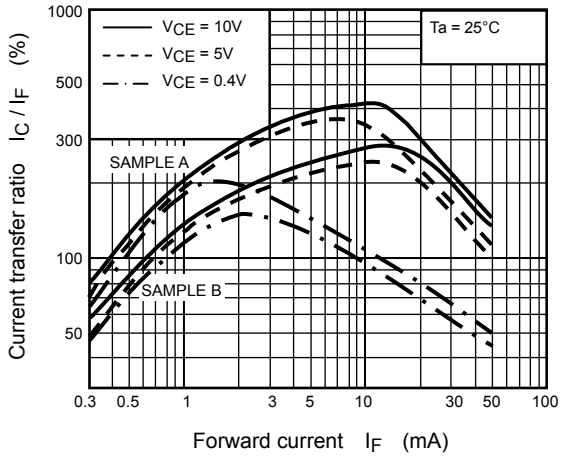
$I_C - V_{CE}$



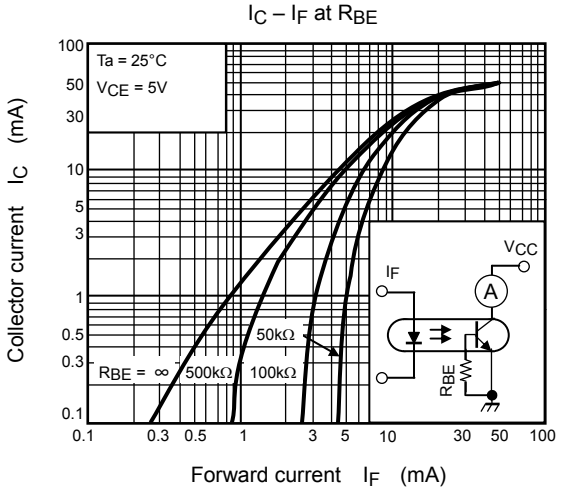
$I_C - I_F$



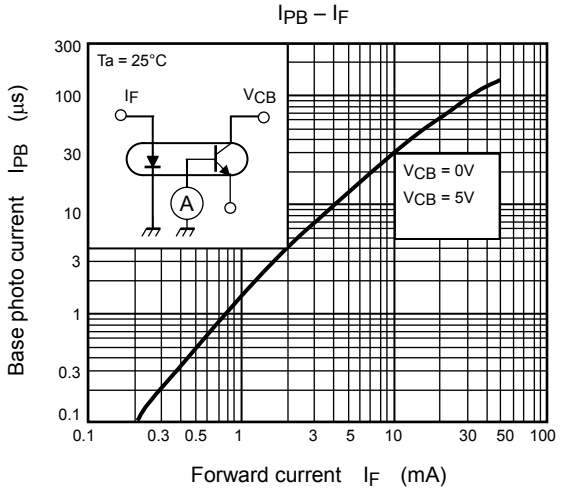
$I_C / I_F - I_F$



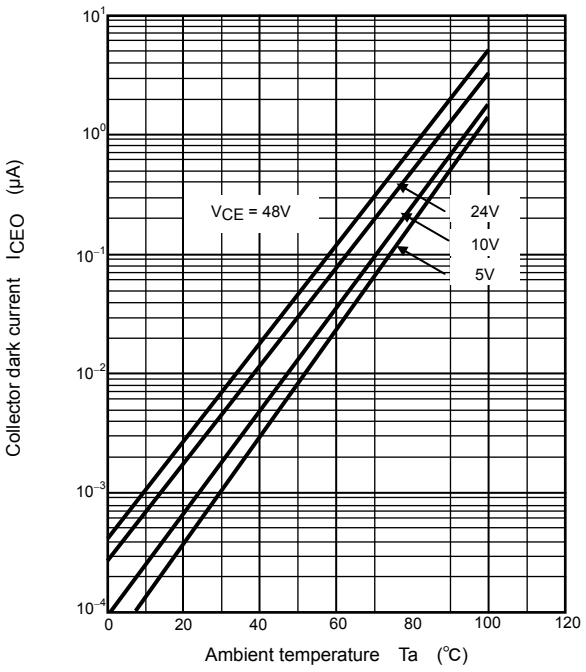
$I_C - I_F$ at R_{BE}



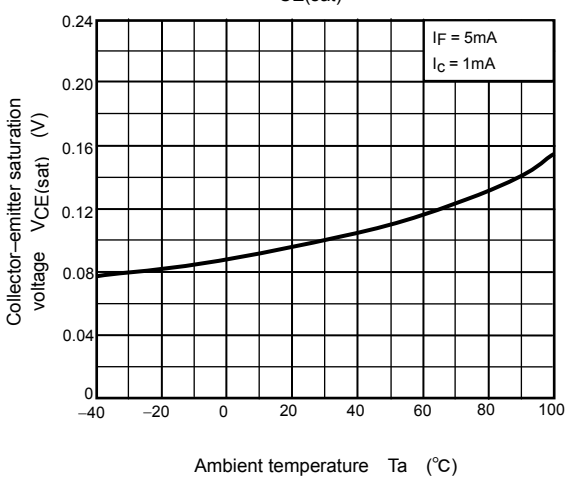
$I_{PB} - I_F$



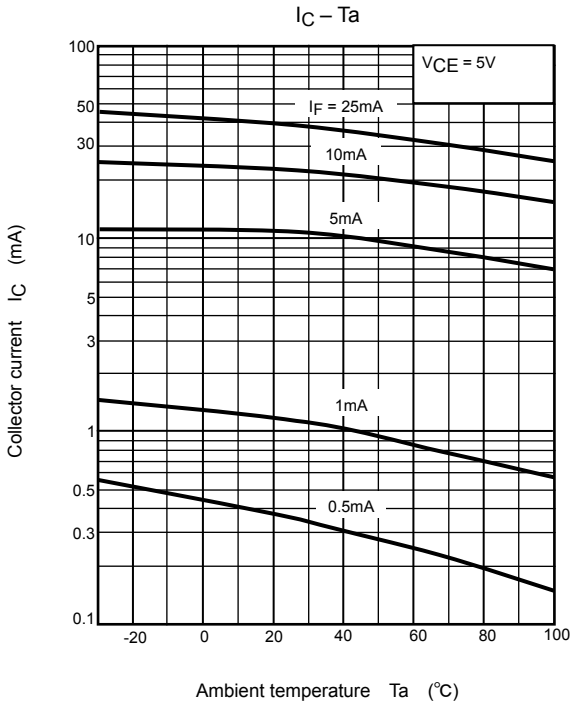
I_{CEO} – Ta



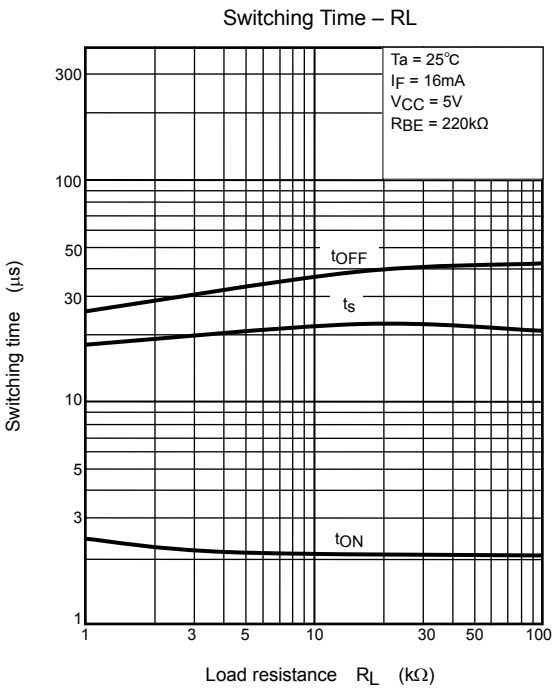
$V_{CE(sat)}$ – Ta



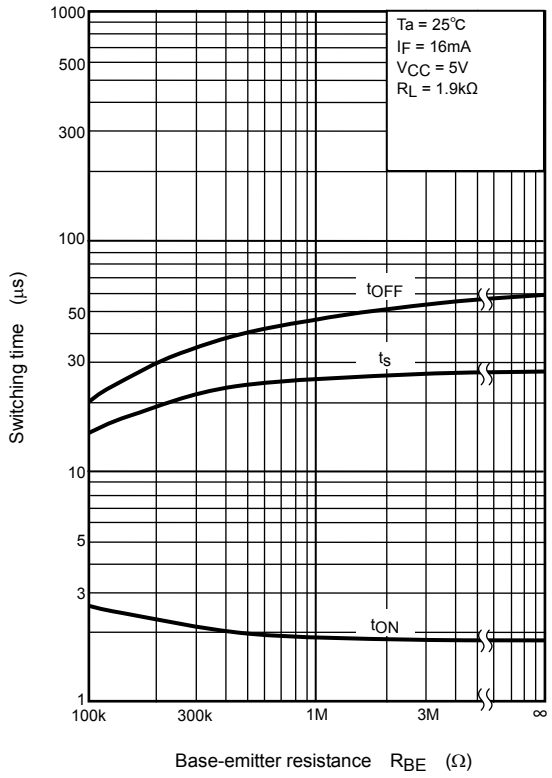
I_C – Ta



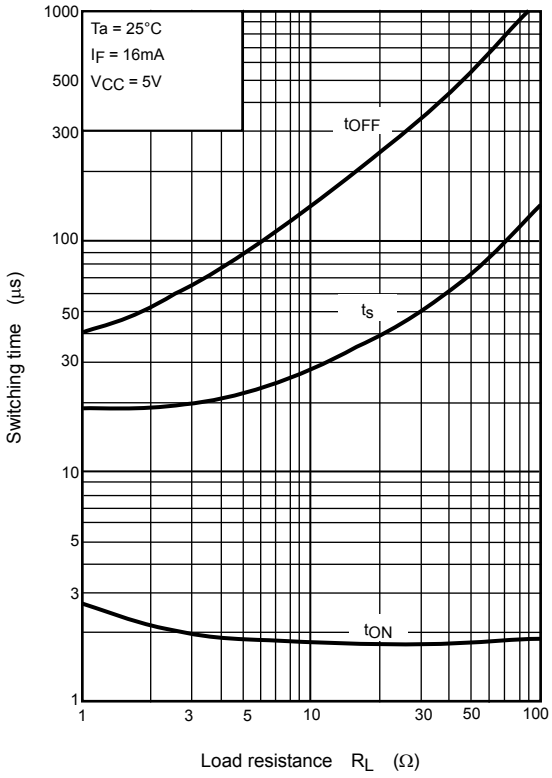
Switching Time – RL



Switching Time – R_{BE}



Switching Time – R_L



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20070701-EN

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